

GF1A - GF1M

GLASS PASSIVATED JUNCTION
SILICON SURFACE MOUNT

PRV : 50 - 1000 Volts
Io : 1.0 Ampere

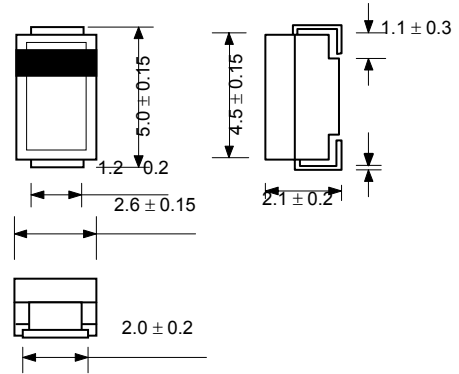
SMA (DO-214AC)

FEATURES :

- * Glass passivated chip
- * High current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SMA Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Lead Formed for Surface Mount
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.067 gram



Dimensions in millimeter

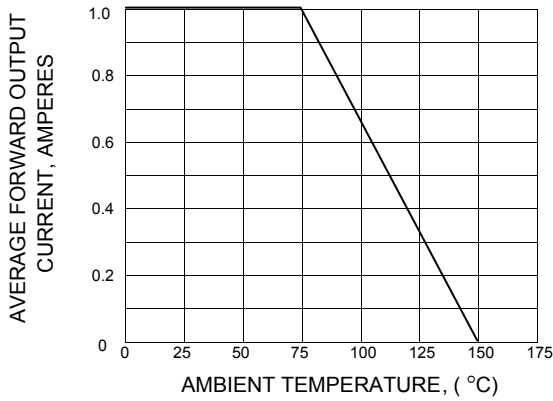
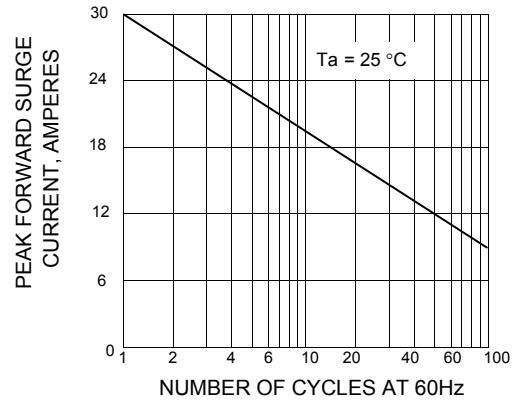
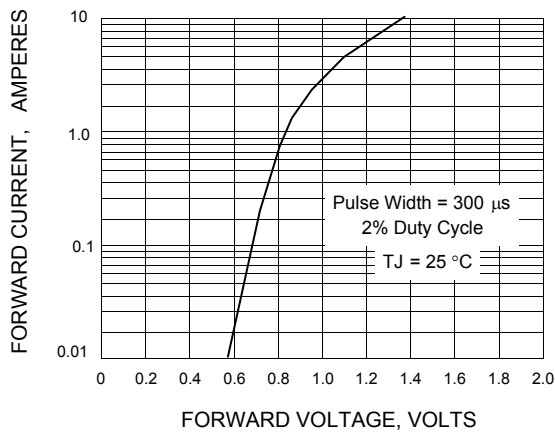
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Sine wave, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20.

RATING	SYMBOL	GF1A	GF1B	GF1D	GF1G	GF1J	GF1K	GF1M	UNIT
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current Ta = 75 °C	I _{F(AV)}	1.0							A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I _{FSM}	30							A
Maximum Forward Voltage at I _F = 1.0 Amp.	V _F	1.0							V
Maximum DC Reverse Current Ta = 25 °C at rated DC Blocking Voltage Ta = 100 °C	I _R	5.0							μA
	I _{R(H)}	50							μA
Typical Reverse Recovery Time (Note 1)	T _{rr}	2.0							μs
Typical Junction Capacitance (Note2)	C _J	8							pF
Junction Temperature Range	T _J	- 65 to + 150							°C
Storage Temperature Range	T _{STG}	- 65 to + 150							°C

Notes :

- (1) Reverse Recovery Test Conditions : I_F = 0.5 A, I_R = 1.0 A, I_{rr} = 0.25 A.
- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Vdc

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

FIG.3 - TYPICAL FORWARD CHARACTERISTICS

FIG.4 - TYPICAL REVERSE CHARACTERISTICS
